

**What is claimed is:**

1. A method of fabricating a liquid crystal display device, comprising:

forming a gate electrode and a gate pad over a substrate;

forming a gate insulating film over the substrate;

forming a semiconductor layer over the gate insulating film;

forming a source electrode, a drain electrode and a data pad over the gate insulating film;

depositing an inorganic insulating material on the gate insulating film;

depositing an organic insulating material over the inorganic insulating material;

removing selectively the organic insulating material at a partial area over the drain electrode, the gate pad and the data pad, to leave a portion of the organic insulating material over the gate pad and the data pad;

patterning the gate insulating film and the inorganic insulating material using at least a portion of the remaining organic insulating material as a mask, thereby providing an inorganic protective film, an organic protective film, a drain contact hole, a gate contact hole and a data contact hole; and

forming a pixel electrode on the inorganic protective film by depositing a transparent conductive film onto the inorganic protective film and the organic protective film and patterning the transparent conductive film, and forming a gate protective electrode and a data protective electrode on the inorganic protective film.

2. The method of claim 1, wherein, in the patterning step, the inorganic insulating material and the organic insulating material are patterned simultaneously.

3. The method of claim 1, wherein the patterning step includes removing a certain thickness of the remaining organic insulating material after the inorganic insulating material has been patterned.

4. The method of claim 1, wherein said inorganic insulating material is silicon nitride.

5. The method of claim 1, wherein said organic insulating material is a photo-sensitive material.

6. The method of claim 5, wherein said photo-sensitive material is acrylic photoresist.

7. The method of claim 1, wherein the step of selectively removing the organic insulating material is performed using a diffracting mask.

8. The method of claim 7, wherein a transmission part of the diffracting mask is positioned in correspondence with the gate contact hole and the drain contact hole, a diffraction part of the diffracting mask is positioned in correspondence with a partial area including the gate pad and the data pad other than the gate contact hole and the data contact hole, and a shielding part of the diffracting mask is

positioned in correspondence with an area other than said partial area.